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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	468
Number of Logic Elements/Cells	3744
Total RAM Bits	18432
Number of I/O	189
Number of Gates	118000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP Exposed Pad
Supplier Device Package	240-RQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k70rc240-2

Notes to tables:
(1) FLEX 10K and FLEX 10KA device package types include plastic J-lead chip carrier (PLCC), thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), ball-grid array (BGA), pin-grid array (PGA), and FineLine BGA™ packages.
(2) This option is supported with a 256-pin FineLine BGA package. By using SameFrame pin migration, all FineLine BGA packages are pin compatible. For example, a board can be designed to support both 256-pin and 484-pin FineLine BGA packages. The Altera software automatically avoids conflicting pins when future migration is set.

General Description

Altera's FLEX 10K devices are the industry's first embedded PLDs. Based on reconfigurable CMOS SRAM elements, the Flexible Logic Element MatriX (FLEX) architecture incorporates all features necessary to implement common gate array megafunctions. With up to 250,000 gates, the FLEX 10K family provides the density, speed, and features to integrate entire systems, including multiple 32-bit buses, into a single device.

FLEX 10K devices are reconfigurable, which allows 100% testing prior to shipment. As a result, the designer is not required to generate test vectors for fault coverage purposes. Additionally, the designer does not need to manage inventories of different ASIC designs; FLEX 10K devices can be configured on the board for the specific functionality required.

Table 6 shows FLEX 10K performance for some common designs. All performance values were obtained with Synopsys DesignWare or LPM functions. No special design technique was required to implement the applications; the designer simply inferred or instantiated a function in a Verilog HDL, VHDL, Altera Hardware Description Language (AHDL), or schematic design file.

Table 6. FLEX 10K & FLEX 10KA Performance

Application	Resources Used		Performance				Units
	LEs	EABs	-1 Speed Grade	-2 Speed Grade	-3 Speed Grade	-4 Speed Grade	
16-bit loadable counter *(1)*	16	0	204	166	125	95	MHz
16-bit accumulator *(1)*	16	0	204	166	125	95	MHz
16-to-1 multiplexer *(2)*	10	0	4.2	5.8	6.0	7.0	ns
256 × 8 RAM read cycle speed *(3)*	0	1	172	145	108	84	MHz
256 × 8 RAM write cycle speed *(3)*	0	1	106	89	68	63	MHz

Notes:
(1) The speed grade of this application is limited because of clock high and low specifications.
(2) This application uses combinatorial inputs and outputs.
(3) This application uses registered inputs and outputs.

Figure 11. LAB Connections to Row & Column Interconnect

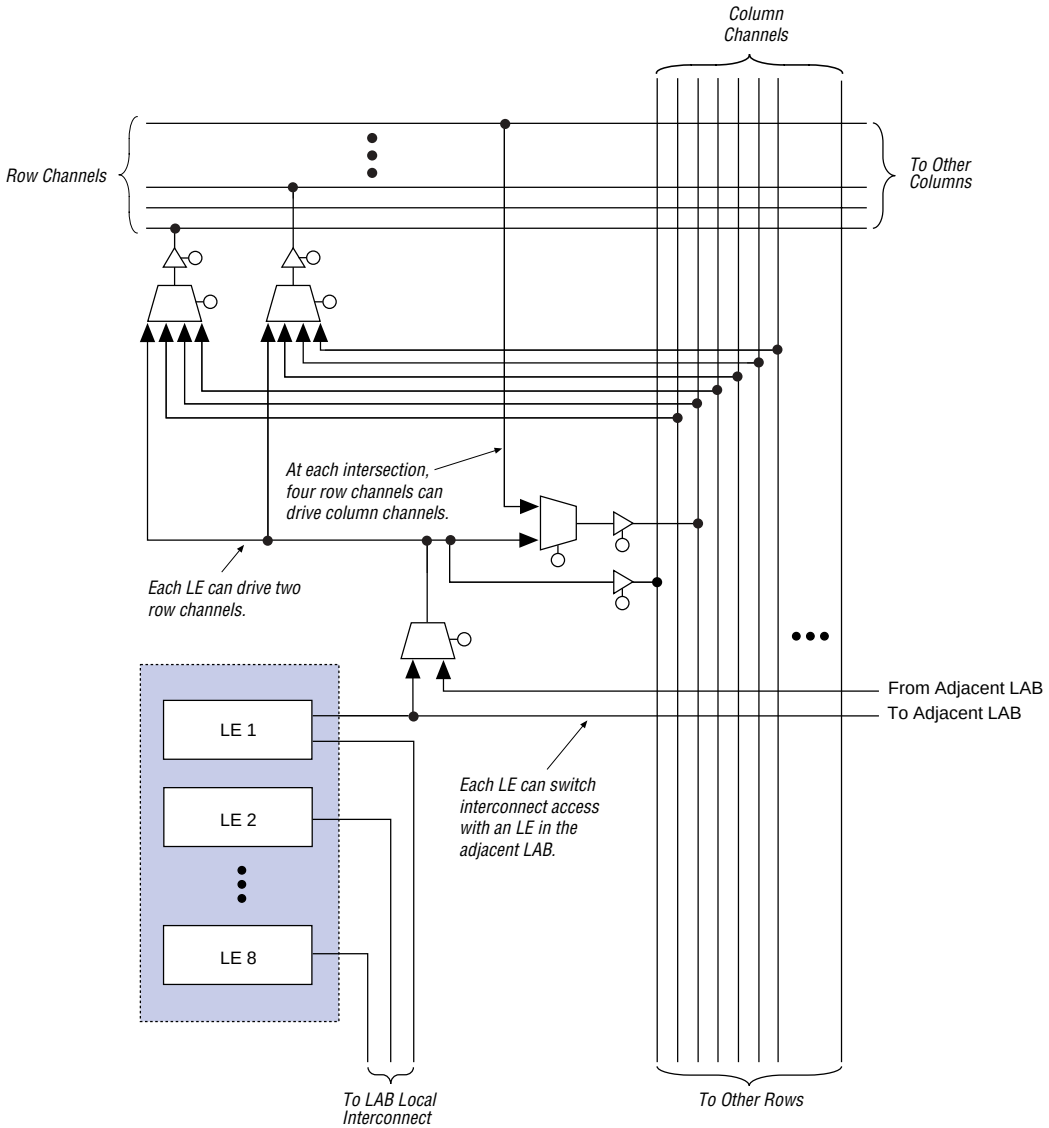


Table 8. EPF10K10, EPF10K20, EPF10K30, EPF10K40 & EPF10K50 Peripheral Bus Sources

Peripheral Control Signal	EPF10K10 EPF10K10A	EPF10K20	EPF10K30 EPF10K30A	EPF10K40	EPF10K50 EPF10K50V
OE0	Row A	Row A	Row A	Row A	Row A
OE1	Row A	Row B	Row B	Row C	Row B
OE2	Row B	Row C	Row C	Row D	Row D
OE3	Row B	Row D	Row D	Row E	Row F
OE4	Row C	Row E	Row E	Row F	Row H
OE5	Row C	Row F	Row F	Row G	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A	Row A	Row B	Row A
CLKENA1/OE6/GLOBAL1	Row A	Row B	Row B	Row C	Row C
CLKENA2/CLR0	Row B	Row C	Row C	Row D	Row E
CLKENA3/OE7/GLOBAL2	Row B	Row D	Row D	Row E	Row G
CLKENA4/CLR1	Row C	Row E	Row E	Row F	Row I
CLKENA5/CLK1/GLOBAL3	Row C	Row F	Row F	Row H	Row J

Table 9. EPF10K70, EPF10K100, EPF10K130V & EPF10K250A Peripheral Bus Sources

Peripheral Control Signal	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
OE0	Row A	Row A	Row C	Row E
OE1	Row B	Row C	Row E	Row G
OE2	Row D	Row E	Row G	Row I
OE3	Row I	Row L	Row N	Row P
OE4	Row G	Row I	Row K	Row M
OE5	Row H	Row K	Row M	Row O
CLKENA0/CLK0/GLOBAL0	Row E	Row F	Row H	Row J
CLKENA1/OE6/GLOBAL1	Row C	Row D	Row F	Row H
CLKENA2/CLR0	Row B	Row B	Row D	Row F
CLKENA3/OE7/GLOBAL2	Row F	Row H	Row J	Row L
CLKENA4/CLR1	Row H	Row J	Row L	Row N
CLKENA5/CLK1/GLOBAL3	Row E	Row G	Row I	Row K

Table 10 lists the FLEX 10K row-to-IOE interconnect resources.

Table 10. FLEX 10K Row-to-IOE Interconnect Resources

Device	Channels per Row (*n*)	Row Channels per Pin (*m*)
EPF10K10 EPF10K10A	144	18
EPF10K20	144	18
EPF10K30 EPF10K30A	216	27
EPF10K40	216	27
EPF10K50 EPF10K50V	216	27
EPF10K70	312	39
EPF10K100 EPF10K100A	312	39
EPF10K130V	312	39
EPF10K250A	456	57

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels that each IOE can access is different for each IOE. See Figure 15.

Figure 15. FLEX 10K Column-to-IOE Connections

The values for m and n are provided in Table 11.

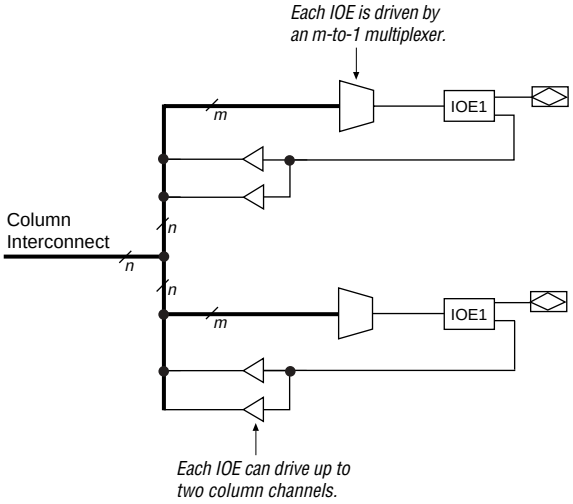


Table 11 lists the FLEX 10K column-to-IOE interconnect resources.

Table 11. FLEX 10K Column-to-IOE Interconnect Resources

Device	Channels per Column (*n*)	Column Channel per Pin (*m*)
EPF10K10 EPF10K10A	24	16
EPF10K20	24	16
EPF10K30 EPF10K30A	24	16
EPF10K40	24	16
EPF10K50 EPF10K50V	24	16
EPF10K70	24	16
EPF10K100 EPF10K100A	24	16
EPF10K130V	32	24
EPF10K250A	40	32

Table 13. FLEX 10K JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern output at the device pins.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the `TDI` and `TDO` pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the `TDI` and `TDO` pins, allowing the USERCODE to be serially shifted out of `TDO`.
IDCODE	Selects the IDCODE register and places it between `TDI` and `TDO`, allowing the IDCODE to be serially shifted out of `TDO`.
ICR Instructions	These instructions are used when configuring a FLEX 10K device via JTAG ports with a BitBlaster, or ByteBlasterMV or MasterBlaster download cable, or using a Jam File (**.jam**) or Jam Byte-Code File (**.jbc**) via an embedded processor.

The instruction register length of FLEX 10K devices is 10 bits. The USERCODE register length in FLEX 10K devices is 32 bits; 7 bits are determined by the user, and 25 bits are predetermined. Tables 14 and 15 show the boundary-scan register length and device IDCODE information for FLEX 10K devices.

Table 14. FLEX 10K Boundary-Scan Register Length

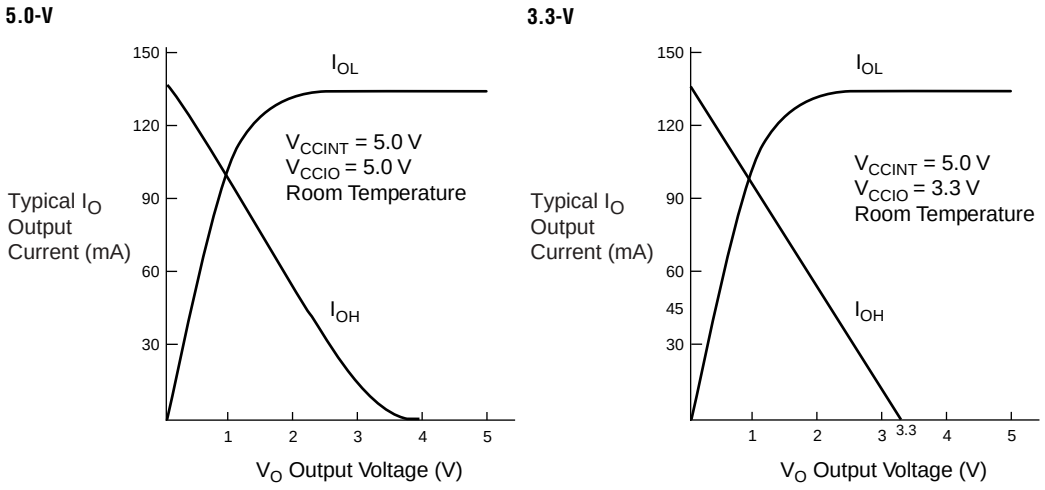
Device	Boundary-Scan Register Length
EPF10K10, EPF10K10A	480
EPF10K20	624
EPF10K30, EPF10K30A	768
EPF10K40	864
EPF10K50, EPF10K50V	960
EPF10K70	1,104
EPF10K100, EPF10K100A	1,248
EPF10K130V	1,440
EPF10K250A	1,440

Notes to tables:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input voltage is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms. V_{CC} must rise monotonically.
(5) Typical values are for T_A = 25° C and V_{CC} = 5.0 V.
(6) These values are specified under the Recommended Operation Condition shown in Table 18 on page 45.
(7) The I_{OH} parameter refers to high-level TTL or CMOS output current.
(8) The I_{OL} parameter refers to low-level TTL or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(9) This value is specified for normal device operation. The value may vary during power-up.
(10) Capacitance is sample-tested only.

Figure 20 shows the typical output drive characteristics of FLEX 10K devices with 5.0-V and 3.3-V V_{CCIO}. The output driver is compliant with the 5.0-V ***PCI Local Bus Specification, Revision 2.2*** (for 5.0-V V_{CCIO}).

Figure 20. Output Drive Characteristics of FLEX 10K Devices



Tables 22 through 25 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for EPF10K50V and EPF10K130V devices.

Table 22. EPF10K50V & EPF10K130V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground *(2)*	–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	Ceramic packages, under bias		150	° C
		RQFP and BGA packages, under bias		135	° C

Table 23. EPF10K50V & EPF10K130V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
V_{CCIO}	Supply voltage for output buffers	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
V_I	Input voltage	*(5)*	-0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Figures 25 through 27 show the delays that correspond to various paths and functions within the LE, IOE, and EAB timing models.

Figure 25. FLEX 10K Device LE Timing Model

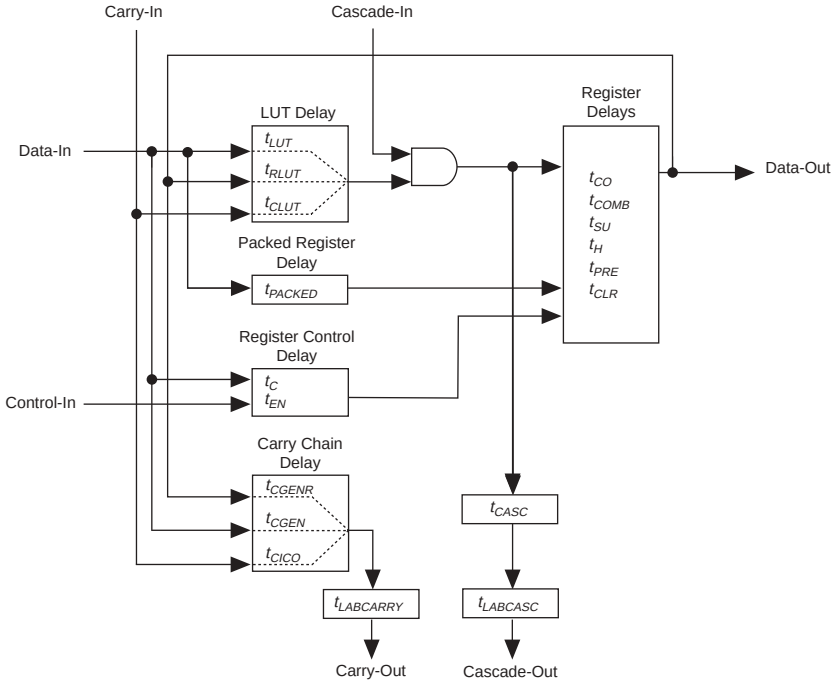
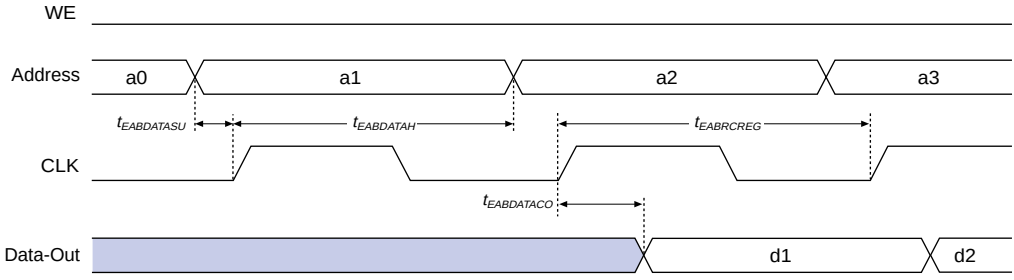


Figure 30. EAB Synchronous Timing Waveforms

EAB Synchronous Read



EAB Synchronous Write (EAB Output Registers Used)

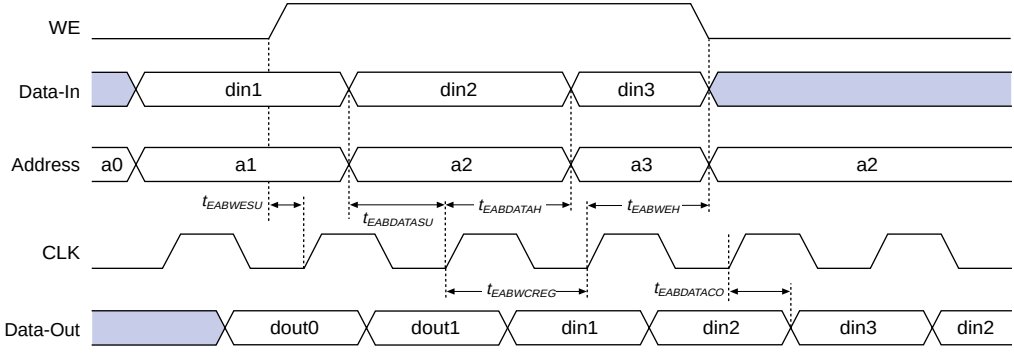


Table 40. EPF10K10 & EPF10K20 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		1.3		1.6	ns
t_{IOC}		0.5		0.7	ns
t_{IOCO}		0.2		0.2	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	2.8		3.2		ns
t_{IOH}	1.0		1.2		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		2.6		3.5	ns
t_{OD2}		4.9		6.4	ns
t_{OD3}		6.3		8.2	ns
t_{XZ}		4.5		5.4	ns
t_{ZX1}		4.5		5.4	ns
t_{ZX2}		6.8		8.3	ns
t_{ZX3}		8.2		10.1	ns
t_{INREG}		6.0		7.5	ns
t_{IOFD}		3.1		3.5	ns
t_{INCOMB}		3.1		3.5	ns

Table 43. EPF10K10 Device Interconnect Timing Microparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
$t_{DIN2IOE}$		4.8		6.2	ns
t_{DIN2LE}		2.6		3.8	ns
$t_{DIN2DATA}$		4.3		5.2	ns
$t_{DCLK2IOE}$		3.4		4.0	ns
$t_{DCLK2LE}$		2.6		3.8	ns
$t_{SAMELAB}$		0.6		0.6	ns
$t_{SAMEROW}$		3.6		3.8	ns
$t_{SAMECOLUMN}$		0.9		1.1	ns
$t_{DIFFROW}$		4.5		4.9	ns
$t_{TWOROWS}$		8.1		8.7	ns
$t_{LEPERIPH}$		3.3		3.9	ns
$t_{LABCARRY}$		0.5		0.8	ns
$t_{LABCASC}$		2.7		3.0	ns

Table 44. EPF10K20 Device Interconnect Timing Microparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
$t_{DIN2IOE}$		5.2		6.6	ns
t_{DIN2LE}		2.6		3.8	ns
$t_{DIN2DATA}$		4.3		5.2	ns
$t_{DCLK2IOE}$		4.3		4.0	ns
$t_{DCLK2LE}$		2.6		3.8	ns
$t_{SAMELAB}$		0.6		0.6	ns
$t_{SAMEROW}$		3.7		3.9	ns
$t_{SAMECOLUMN}$		1.4		1.6	ns
$t_{DIFFROW}$		5.1		5.5	ns
$t_{TWOROWS}$		8.8		9.4	ns
$t_{LEPERIPH}$		4.7		5.6	ns
$t_{LABCARRY}$		0.5		0.8	ns
$t_{LABCASC}$		2.7		3.0	ns

Table 49. EPF10K30, EPF10K40 & EPF10K50 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		0.4		0.6	ns
t_{IOC}		0.5		0.9	ns
t_{IOCO}		0.4		0.5	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	3.1		3.5		ns
t_{IOH}	1.0		1.9		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		3.3		3.6	ns
t_{OD2}		5.6		6.5	ns
t_{OD3}		7.0		8.3	ns
t_{XZ}		5.2		5.5	ns
t_{ZX1}		5.2		5.5	ns
t_{ZX2}		7.5		8.4	ns
t_{ZX3}		8.9		10.2	ns
t_{INREG}		7.7		10.0	ns
t_{IOFD}		3.3		4.0	ns
t_{INCOMB}		3.3		4.0	ns

Table 50. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.9	ns
$t_{EABDATA2}$		4.8		6.0	ns
t_{EABWE1}		1.0		1.2	ns
t_{EABWE2}		5.0		6.2	ns
t_{EABCLK}		1.0		2.2	ns
t_{EABCO}		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.9	ns
t_{EABSU}	1.5		1.8		ns
t_{EABH}	2.0		2.5		ns
t_{AA}		8.7		10.7	ns
t_{WP}	5.8		7.2		ns
t_{WDSU}	1.6		2.0		ns
t_{WDH}	0.3		0.4		ns
t_{WASU}	0.5		0.6		ns
t_{WAH}	1.0		1.2		ns
t_{WO}		5.0		6.2	ns
t_{DD}		5.0		6.2	ns
t_{EABOUT}		0.5		0.6	ns
t_{EABCH}	4.0		4.0		ns
t_{EABCL}	5.8		7.2		ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 57 through 63 show EPF10K70 device internal and external timing parameters.

Table 57. EPF10K70 Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.5		1.6		2.0	ns
t_{PACKED}		0.8		0.9		1.3	ns
t_{EN}		0.8		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.0		1.1		1.4	ns
t_{CGENR}		1.1		1.2		1.5	ns
t_{CASC}		1.0		1.1		1.3	ns
t_{C}		0.7		0.8		1.0	ns
t_{CO}		0.9		1.0		1.4	ns
t_{COMB}		0.4		0.5		0.7	ns
t_{SU}	1.9		2.1		2.6		ns
t_{H}	2.1		2.3		3.1		ns
t_{PRE}		0.9		1.0		1.4	ns
t_{CLR}		0.9		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 72. EPF10K50V Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.2		1.6		1.9		2.1	ns
t_{IOC}		0.3		0.4		0.5		0.5	ns
t_{IOCO}		0.3		0.3		0.4		0.4	ns
t_{IOCOMB}		0.0		0.0		0.0		0.0	ns
t_{IOSU}	2.8		2.8		3.4		3.9		ns
t_{IOH}	0.7		0.8		1.0		1.4		ns
t_{IOCLR}		0.5		0.6		0.7		0.7	ns
t_{OD1}		2.8		3.2		3.9		4.7	ns
t_{OD2}		–		–		–		–	ns
t_{OD3}		6.5		6.9		7.6		8.4	ns
t_{XZ}		2.8		3.1		3.8		4.6	ns
t_{ZX1}		2.8		3.1		3.8		4.6	ns
t_{ZX2}		–		–		–		–	ns
t_{ZX3}		6.5		6.8		7.5		8.3	ns
t_{INREG}		5.0		5.7		7.0		9.0	ns
t_{IOFD}		1.5		1.9		2.3		2.7	ns
t_{INCOMB}		1.5		1.9		2.3		2.7	ns

Table 82. EPF10K130V Device Interconnect Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		8.0		9.0		9.5	ns
t_{DIN2LE}		2.4		3.0		3.1	ns
$t_{DIN2DATA}$		5.0		6.3		7.4	ns
$t_{DCLK2IOE}$		3.6		4.6		5.1	ns
$t_{DCLK2LE}$		2.4		3.0		3.1	ns
$t_{SAMELAB}$		0.4		0.6		0.8	ns
$t_{SAMEROW}$		4.5		5.3		6.5	ns
$t_{SAMECOLUMN}$		9.0		9.5		9.7	ns
$t_{DIFFROW}$		13.5		14.8		16.2	ns
$t_{TWOROWS}$		18.0		20.1		22.7	ns
$t_{LEPERIPH}$		8.1		8.6		9.5	ns
$t_{LABCARRY}$		0.6		0.8		1.0	ns
$t_{LABCASC}$		0.8		1.0		1.2	ns

Table 83. EPF10K130V Device External Timing Parameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		15.0		19.1		24.2	ns
t_{INSU} *(2)*, *(3)*	6.9		8.6		11.0		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	7.8	2.0	9.9	2.0	11.3	ns

Table 84. EPF10K130V Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	6.7		8.5		10.8		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	6.9	2.0	8.8	2.0	10.2	ns
$t_{XZBIDIR}$		12.9		16.4		19.3	ns
$t_{ZXBIDIR}$		12.9		16.4		19.3	ns

Table 94. EPF10K30A Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		5.5		6.5		8.5	ns
$t_{EABDATA2}$		1.1		1.3		1.8	ns
t_{EABWE1}		2.4		2.8		3.7	ns
t_{EABWE2}		2.1		2.5		3.2	ns
t_{EABCLK}		0.0		0.0		0.2	ns
t_{EABCO}		1.7		2.0		2.6	ns
$t_{EABBYPASS}$		0.0		0.0		0.3	ns
t_{EABSU}	1.2		1.4		1.9		ns
t_{EABH}	0.1		0.1		0.3		ns
t_{AA}		4.2		5.0		6.5	ns
t_{WP}	3.8		4.5		5.9		ns
t_{WDSU}	0.1		0.1		0.2		ns
t_{WDH}	0.1		0.1		0.2		ns
t_{WASU}	0.1		0.1		0.2		ns
t_{WAH}	0.1		0.1		0.2		ns
t_{WO}		3.7		4.4		6.4	ns
t_{DD}		3.7		4.4		6.4	ns
t_{EABOUT}		0.0		0.1		0.6	ns
t_{EABCH}	3.0		3.5		4.0		ns
t_{EABCL}	3.8		4.5		5.9		ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 99 through 105 show EPF10K100A device internal and external timing parameters.

Table 99. EPF10K100A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.0		1.2		1.4	ns
t_{CLUT}		0.8		0.9		1.1	ns
t_{RLUT}		1.4		1.6		1.9	ns
t_{PACKED}		0.4		0.5		0.5	ns
t_{EN}		0.6		0.7		0.8	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.4		0.4		0.6	ns
t_{CGENR}		0.6		0.7		0.8	ns
t_{CASC}		0.7		0.9		1.0	ns
t_{C}		0.9		1.0		1.2	ns
t_{CO}		0.2		0.3		0.3	ns
t_{COMB}		0.6		0.7		0.8	ns
t_{SU}	0.8		1.0		1.2		ns
t_{H}	0.3		0.5		0.5		ns
t_{PRE}		0.3		0.3		0.4	ns
t_{CLR}		0.3		0.3		0.4	ns
t_{CH}	2.5		3.5		4.0		ns
t_{CL}	2.5		3.5		4.0		ns

Table 113. ClockLock & ClockBoost Parameters (Part 2 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
$f_{CLKDEV1}$	Input deviation from user specification in MAX+PLUS II (ClockBoost clock multiplication factor equals 1) *(1)*			±1	MHz
$f_{CLKDEV2}$	Input deviation from user specification in MAX+PLUS II (ClockBoost clock multiplication factor equals 2) *(1)*			±0.5	MHz
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)			100	ps
t_{LOCK}	Time required for ClockLock or ClockBoost to acquire lock *(2)*			10	µs
t_{JITTER}	Jitter on ClockLock or ClockBoost-generated clock *(3)*			1	ns
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock	40	50	60	%

Notes:

(1) To implement the ClockLock and ClockBoost circuitry with the MAX+PLUS II software, designers must specify the input frequency. The MAX+PLUS II software tunes the PLL in the ClockLock and ClockBoost circuitry to this frequency. The f_{CLKDEV} parameter specifies how much the incoming clock can differ from the specified frequency during device operation. Simulation does not reflect this parameter.

(2) During device configuration, the ClockLock and ClockBoost circuitry is configured before the rest of the device. If the incoming clock is supplied during configuration, the ClockLock and ClockBoost circuitry locks during configuration, because the t_{LOCK} value is less than the time required for configuration.

(3) The t_{JITTER} specification is measured under long-term observation.

Power Consumption

The supply power (P) for FLEX 10K devices can be calculated with the following equation:

$$P = P_{INT} + P_{IO} = (I_{CCSTANDBY} + I_{CCACTIVE}) \times V_{CC} + P_{IO}$$

Typical $I_{CCSTANDBY}$ values are shown as I_{CC0} in the FLEX 10K device DC operating conditions tables on pages 46, 49, and 52 of this data sheet. The $I_{CCACTIVE}$ value depends on the switching frequency and the application logic. This value is calculated based on the amount of current that each LE typically consumes. The P_{IO} value, which depends on the device output load characteristics and switching frequency, can be calculated using the guidelines given in *Application Note 74 (Evaluating Power for Altera Devices)*.

Compared to the rest of the device, the embedded array consumes a negligible amount of power. Therefore, the embedded array can be ignored when calculating supply current.

The $I_{CCACTIVE}$ value is calculated with the following equation:

$$I_{CCACTIVE} = K \times \mathbf{f_{MAX}} \times N \times \mathbf{tog_{LC}} \times \frac{\mu A}{MHz \times LE}$$

The parameters in this equation are shown below: